

NPN DARLINGTON POWER SILICON TRANSISTOR

Qualified per MIL-PRF-19500/472

Devices

2N6350 2N6351 2N6352 2N6353

Qualified Level

**JAN
JANTX
JANTXV**

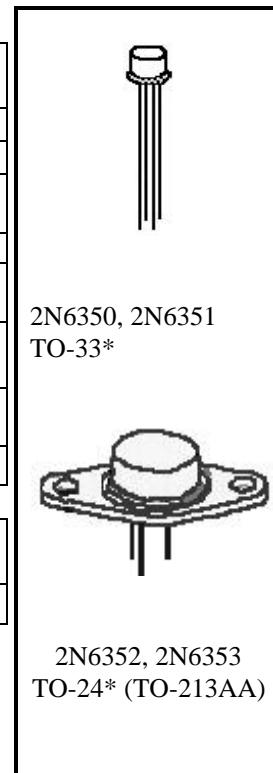
MAXIMUM RATINGS

Ratings	Symbol	2N6350 2N6352	2N6351 2N6353	Units
Collector-Emitter Voltage	V _{CER}	80	150	Vdc
Collector-Base Voltage	V _{CBO}	80	150	Vdc
Emitter-Base Voltage	V _{EBO}	12	6.0	Vdc
Base Current	I _B	0.5		Adc
Collector Current	I _C	5.0 10 ⁽¹⁾		Adc Adc
		2N6350 2N6351	2N6352 2N6353	
Total Power Dissipation @ T _A = 25°C @ T _C = 100°C	P _T	1.0 ⁽²⁾ 5.0 ⁽³⁾	2.0 ⁽⁴⁾ 25 ⁽⁵⁾	W W
Operating & Storage Junction Temperature Range	T _J , T _{Stg}	-65 to +200		°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	2N6350 2N6351	2N6352 2N6353	Unit
Thermal Resistance, Junction-to-Case	R _{θJC}	20	4.0	°C/W

- 1) Applies for t_p ≤ 10 ms, Duty cycle ≤ 50%
- 2) Derate linearly @ 5.72 mW/°C above T_A > 25°C
- 3) Derate linearly @ 50 mW/°C above T_C > 100°C
- 4) Derate linearly @ 11.4 mW/°C above T_A > 25°C
- 5) Derate linearly @ 250 mW/°C above T_C > 100°C



*See Appendix A for package outline

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage I _C = 25 mA, R _{BIE} = 2.2 kΩ, R _{B2E} = 100 Ω	V _{(BR)CER}	80 150		Vdc

2N6350, 2N6351, 2N6352, 2N6353 JAN SERIES

ELECTRICAL CHARACTERISTICS (con't)

Characteristics	Symbol	Min.	Max.	Unit
Emitter-Base Breakdown Voltage I _{EB} = 12 mAdc, Base 1 Open I _{EB} = 12 mAdc, Base 2 Open	V _{(BR)EBO}	6.0 12		Vdc
Collector-Emitter Cutoff Current V _{EB1} = 2.0 Vdc, R _{B2E} = 100 Ω, V _{CE} = 80 Vdc 2N6350, 2N6352 V _{EB1} = 2.0 Vdc, R _{B2E} = 100 Ω, V _{CE} = 150 Vdc 2N6351, 2N6353	I _{CEX}		1.0 1.0	μAdc

ON CHARACTERISTICS ⁽⁶⁾

Forward-Current Transfer Ratio I _C = 1.0 Adc, V _{CE} = 5.0 Vdc, R _{B2E} = 1.0 Ω 2N6350, 2N6352 I _C = 5.0 Adc, V _{CE} = 5.0 Vdc, R _{B2E} = 100 Ω I _C = 10 Adc, V _{CE} = 5.0 Vdc, R _{B2E} = 100 Ω	h _{FE}	2,000 2,000 400	10,000	
I _C = 1.0 Adc, V _{CE} = 5.0 Vdc, R _{B2E} = 1.0 Ω 2N6351, 2N6353 I _C = 5.0 Adc, V _{CE} = 5.0 Vdc, R _{B2E} = 100 Ω I _C = 10 Adc, V _{CE} = 5.0 Vdc, R _{B2E} = 100 Ω		1,000 1,000 200	10,000	
Collector-Emitter Saturation Voltage I _C = 5.0 Adc, R _{B2E} = 100 Ω, I _{B1} = 5.0 mA 2N6350, 2N6352 I _C = 5.0 Adc, R _{B2E} = 100 Ω, I _{B1} = 10 mA 2N6351, 2N6353	V _{CE(sat)}		1.5 2.5	Vdc
Base-Emitter Voltage I _C = 5.0 Adc, V _{CE} = 5.0 Vdc, R _{B2E} = 100 Ω	V _{BE1(on)}		2.5	Vdc

DYNAMIC CHARACTERISTICS

Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio I _C = 1.0 Adc, V _{CE} = 10 Vdc, R _{B2E} = 100 Ω; f = 10 MHz	h _{fe}	5.0	25	
Output Capacitance V _{CB1} = 10 Vdc, 100 kHz ≤ f ≤ 1.0 MHz, Base 2 Open	C _{obo}		120	pF

SWITCHING CHARACTERISTICS

Turn-On Time V _{CC} = 30 Vdc; I _C = 5.0 Adc (See fig 4 for 2N6350, 2N6352) (See fig 5 for 2N6350, 2N6352)	t _{on}		0.5	μs
Turn-Off Time V _{CC} = 30 Vdc; I _C = 5.0 Adc (See fig 4 for 2N6350, 2N6352) (See fig 5 for 2N6350, 2N6352)	t _{off}		1.2	μs

SAFE OPERATING AREA

DC Tests				
T _C = +100°C, 1 Cycle, t ≥ 1.0 s, t _r + t _f = 10 μs, R _{B2E} = 100 Ω (See fig 6 for 2N6350, 2N6351)				
Test 1				
V _{CE} = 1.5 Vdc, I _C = 3.3 Adc	2N6350, 2N6351			
Test 2				
V _{CE} = 30 Vdc, I _C = 167 mA	2N6350, 2N6351			
Test 3				
V _{CE} = 80 Vdc, I _C = 35 mA	2N6350			
Test 4				
V _{CE} = 150 Vdc, I _C = 13 mA	2N6351			
T_C = +100°C, 1 Cycle, t ≥ 1.0 s, t_r + t_f = 10 μs, R_{B2E} = 100 Ω (See fig 7 for 2N6352, 2N6353)				
Test 1				
V _{CE} = 5.0 Vdc, I _C = 5.0 Adc	2N6352, 2N6353			
Test 2				
V _{CE} = 10 Vdc, I _C = 2.5 Adc	2N6352, 2N6353			
Test 3				
V _{CE} = 80 Vdc, I _C = 95 mA	2N6352			
Test 4				
V _{CE} = 150 Vdc, I _C = 35 mA	2N6353			

(6) Pulse Test: Pulse Width = 300μs, Duty Cycle ≤ 2.0%.

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